

Vishay Siliconix

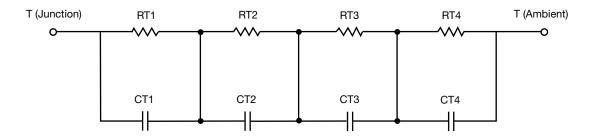
## **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	n/a	79.7957m	n/a		
RT2	n/a	97.1095m	n/a		
RT3	n/a	98.4146m	n/a		
RT4	n/a	124.0081m	n/a		
·	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	99.8502m	n/a		
CT2	n/a	9.0473m	n/a		
CT3	n/a	73.4198m	n/a		
CT4	n/a	268.8670m	n/a		

Note

• n/a indicates not applicable

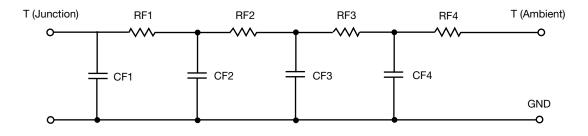
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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### **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



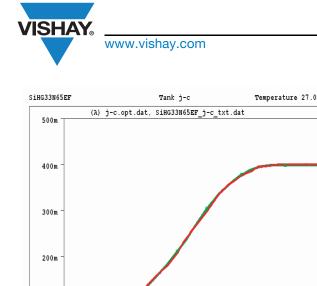
R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	n/a	81.5625m	n/a		
RF2	n/a	17.8245m	n/a		
RF3	n/a	114.7125m	n/a		
RF4	n/a	182.2706m	n/a		
·	THERMAL CAPACI	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	6.1616m	n/a		
CF2	n/a	6.9945m	n/a		
CF3	n/a	3.3366m	n/a		
CF4	n/a	87.8481m	n/a		

Note

• n/a indicates not applicable

# SiHG33N65EF\_RC

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10ms

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September 24, 2015

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